United Monolithic Semiconductors

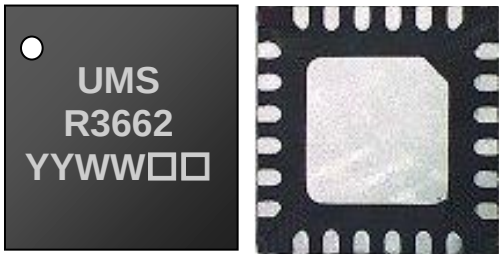
CHR3662-QDG

7-16GHz Integrated Down Converter

GaAs Monolithic Microwave IC in SMD leadless package

Description

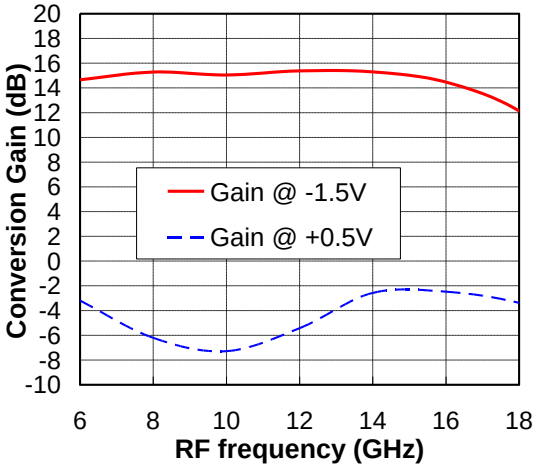
The CHR3662-QDG is a multifunction part which integrates a balanced cold FET mixer, a LO buffer, and a RF LNA including gain control.
It is designed for a wide range of applications, typically commercial communication systems. The circuit is manufactured with a pHEMT process 0.25µm.



It is available in lead-free SMD package.

Main Features

- Broadband RF performance 7-16GHz
- 13dB gain
- 15dBc Image Frequency Rejection
- 0dBm Input IP3
- 15dB Gain control
- 24LQFN4x4
- ESD protected
- MSL Level: 1



Main Characteristics

Tamb = +25°C, Vd= 4.5V

Symbol	Parameter	Min	Typ	Max	Unit
F_{RF}	RF frequency range	7		16	GHz
F_{LO}	LO frequency range	4.5		19.5	GHz
F_{IF}	IF frequency range	DC		3.5	GHz
G_c	Conversion gain maximum	11	14		dB

ESD Protections: Electrostatic discharge sensitive device observe handling precautions!

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Electrical Characteristics

Tamb = +25°C, Vd= 4.5V

Symbol	Parameter	Min	Typ	Max	Unit
F_{RF}	RF frequency range	7		16	GHz
F_{LO}	LO frequency range	4.5		19.5	GHz
F_{IF}	IF frequency range	DC		3.5	GHz
G_c	Conversion gain @ V2_V3=-1.5V (1) (gain max) Conversion gain @ V2_V3=+0.5V (1) (gain min)	11	14 -4	 -2	dB dB
ΔG	Gain control range	13	15		dB
NF	Noise Figure @ V2_V3=-1.5V (gain max), for IF>0.1GHz		3	3.5	dB
IFR	Image Frequency Rejection (1)	13	15		dBc
P_{LO}	LO Input power		0		dBm
IIP3	Input IP3@ gain max. Input IP3 all attenuation		0 -3		dBm
LO RL	LO Return Loss		-7	-6	dB
RF RL	RF Return Loss @ Gain max RF Return Loss @ Gain min		-9 -5	-6 -4	dB
LO/RF	LO leakage at RF port @ max. gain		-35		dBm
Vd	DC drain voltage		4.5		V
Id	Drain current	210	280	350	mA
VG	DC gate voltage LNA		-0.3		V
V2_V3	DC gain control voltage	-1.5		0.5	V
B	DC gate control voltage LO buffer		-5		V
VGM	DC gate voltage mixer		-1		V

(1) An external combiner 90° is necessary on I / Q.

Note: Id is not affected by V2, V3.

These values are representative of onboard measurements as defined on the drawing given in the paragraph "Evaluation mother board".

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Absolute Maximum Ratings (1)

Tamb = +25°C

Symbol	Parameter	Values	Unit
Vd	Maximum drain bias voltage	5	V
Id	Maximum drain bias current	400	mA
VG, VGM	Gate bias voltage range	-2.0 to +0.6	V
V2,V3	Gain control voltage range	-2.0 to +1	V
P_RF	Maximum peak input power overdrive	10	dBm
P_{LO}	Maximum LO input power	10	dBm
Tch	Maximum channel temperature	175	°C
Ta	Operating temperature range	-40 to +85	°C
Tstg	Storage temperature range	-55 to +150	°C

(1) Operation of this device above anyone of these parameters may cause permanent damage.

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Device thermal performances

All the figures given in this section are obtained assuming that the QFN device is cooled down only by conduction through the package thermal pad (no convection mode considered).
The temperature is monitored at the package back-side interface (Tcase) as shown below.
The system maximum temperature must be adjusted in order to guarantee that Tcase remains below than the maximum value specified in the next table. So, the system PCB must be designed to comply with this requirement.

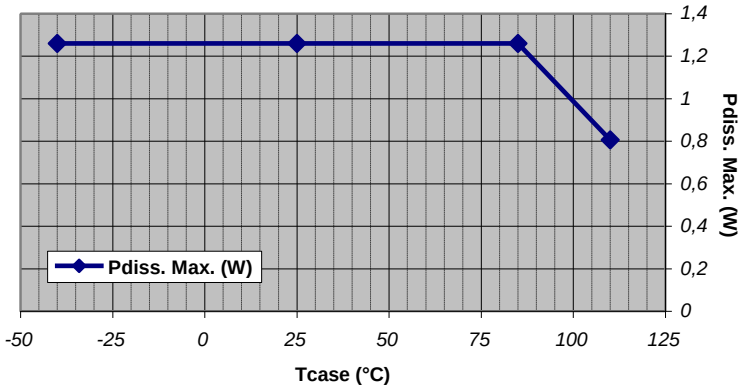
A derating must be applied on the dissipated power if the Tcase temperature can not be maintained below than the maximum temperature specified (see the curve Pdiss. Max) in order to guarantee the nominal device life time (MTTF).

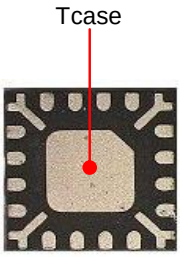
DEVICE THERMAL SPECIFICATION : CHR3662-QDG				
Max. junction temperature (Tj max)			:	154 °C
Max. continuous dissipated power @ Tcase=	85	°C	:	1,26 W
=> Pdiss derating above Tcase(1)=	85	°C	:	18 mW/°C
Junction-Case thermal resistance (Rth J-C)(2)			:	<55 °C/W
Min. package back side operating temperature(3)			:	-40 °C
Max. package back side operating temperature(3)			:	85 °C
Min. storage temperature			:	-55 °C
Max. storage temperature			:	125 °C

(1) Derating at junction temperature constant = Tj max.

*(2) Rth J-C is calculated for a worst case where the **hotter junction** of the MMIC is considered.*

(3) Tcase=Package back side temperature measured under the die-attach-pad (see the drawing below).





Example of QFN 16L 3x3 back-side view, temperature reference point (Tcase) location.

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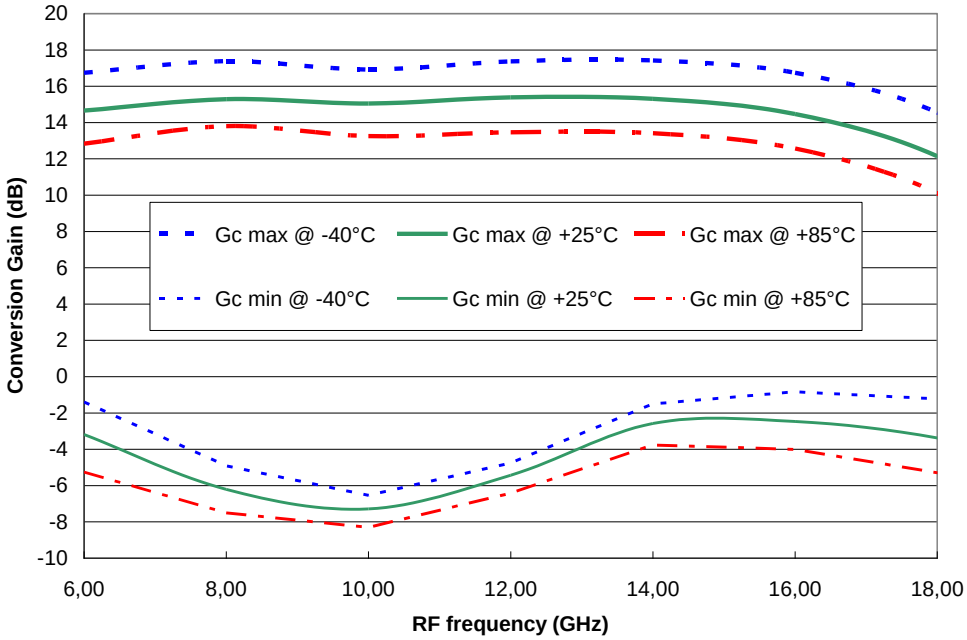
Typical Measured Performances

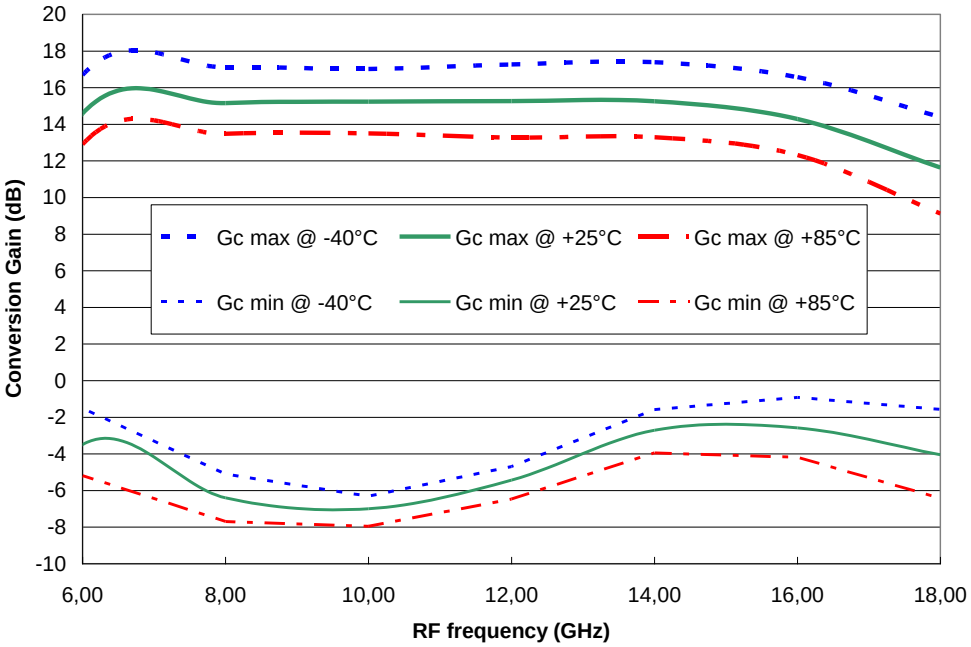
Tamb = +25°C, VD = 4.5V, Typical B = -5V & VG = -0.3V & VGM = -1V, P_LO=0dBm

These values are representative of onboard measurements (on connectors access planes) as defined on the drawing 97342 page 14. The board loss is estimated to 0.5 to 1.5dB in the frequency range.

Conversion Gain @ Freq_IF= 2GHz, F_RF= F_LO + F_IF versus gain control & temperature



Conversion Gain @ Freq_IF= 2GHz, F_RF= F_LO - F_IF versus gain control & temperature



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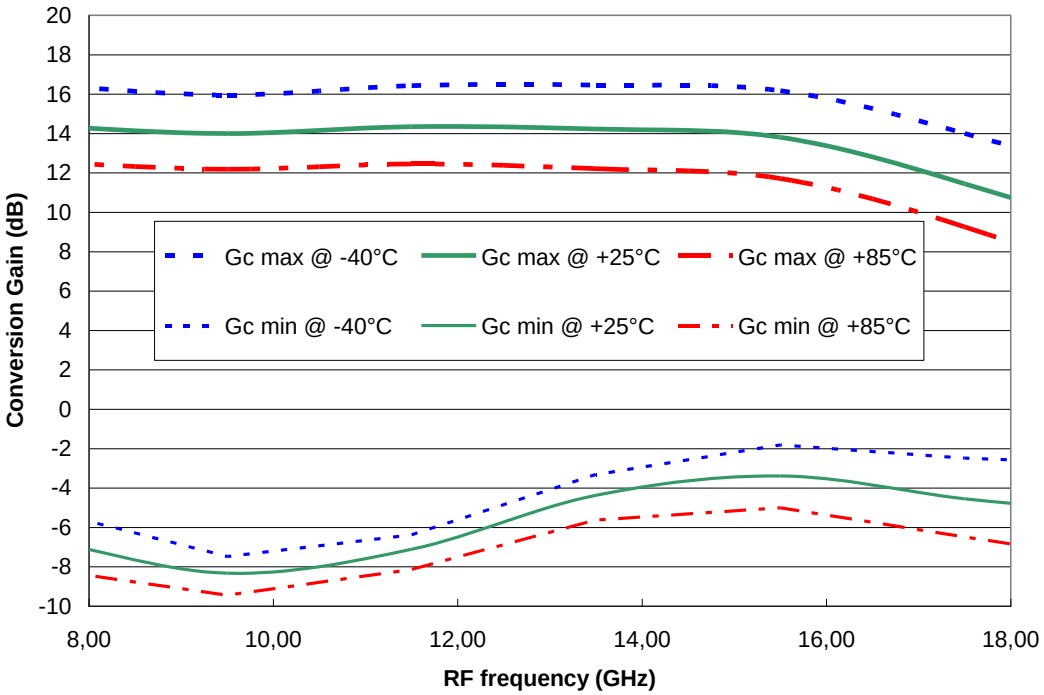
Conversion Gain @ Freq_IF= 3.5GHz, F_RF= F_LO + F_IF
versus gain control & temperature



Conversion Gain @ Freq_IF= 3.5GHz, F_RF= F_LO - F_IF
versus gain control & temperature

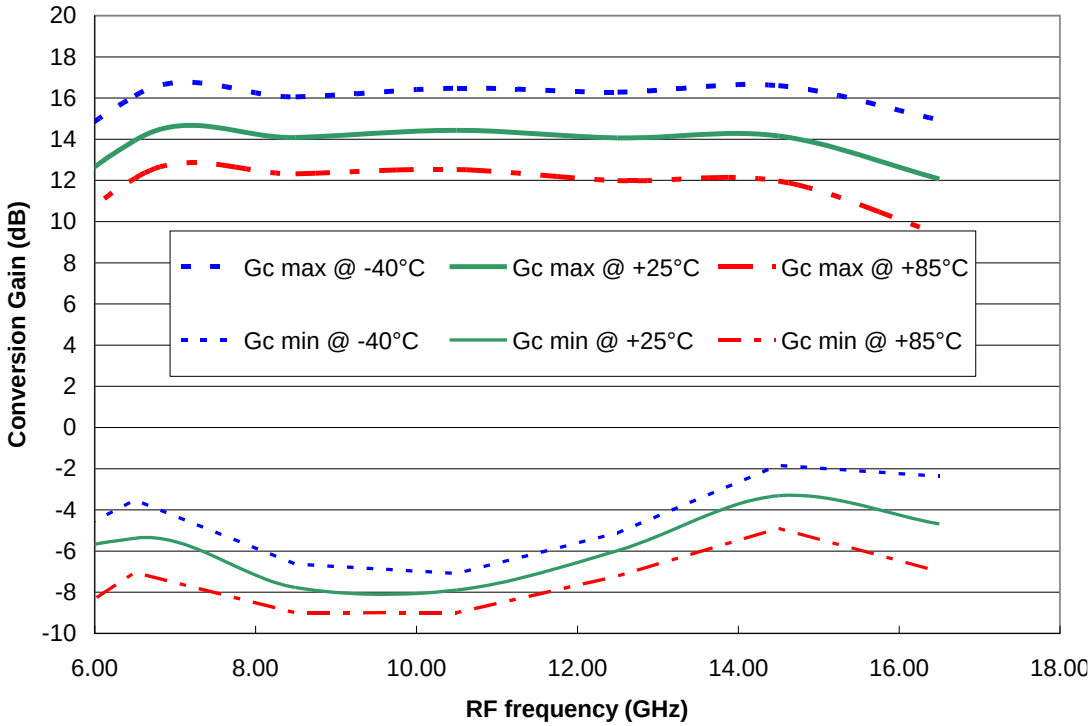


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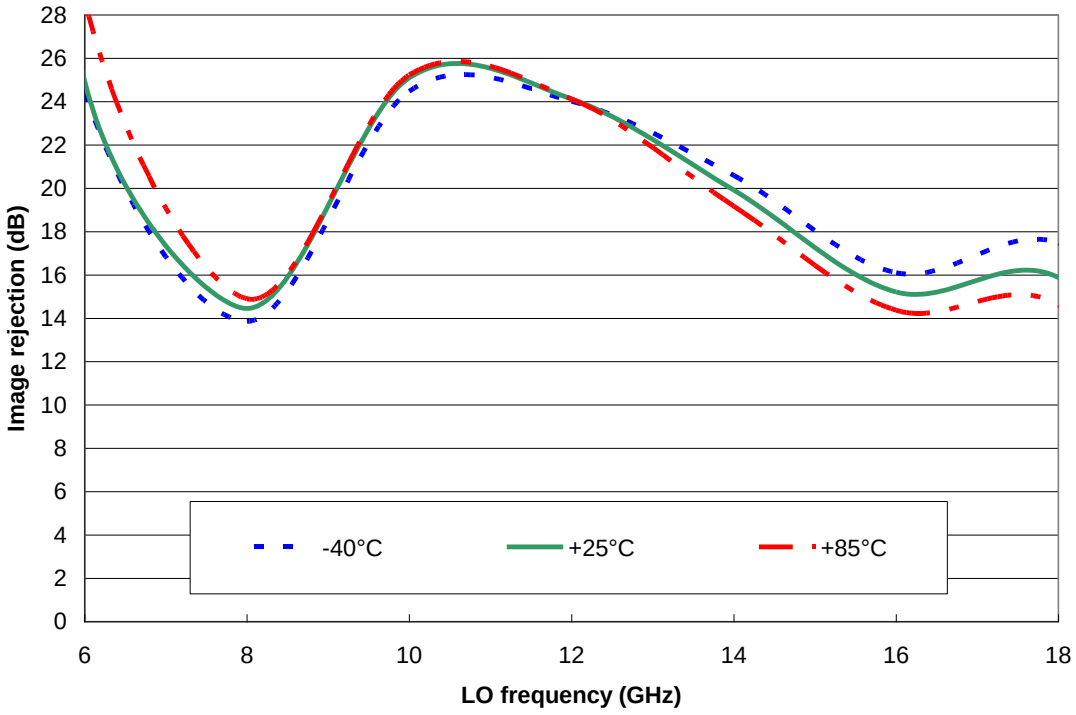
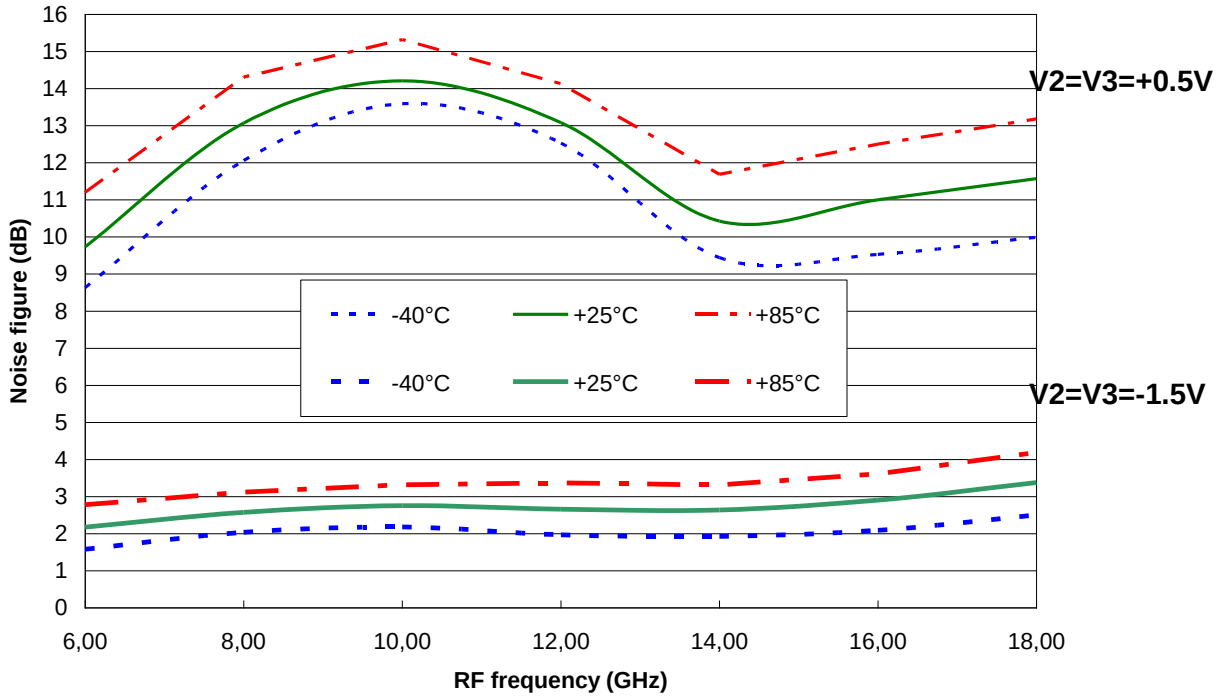
Image rejection @ Freq_IF= 2GHz, V2=V3=-1.5V versus temperature



Noise figure @ Freq_IF= 2GHz versus gain & temperature



Rem: The losses due to board are removed for noise measurements.

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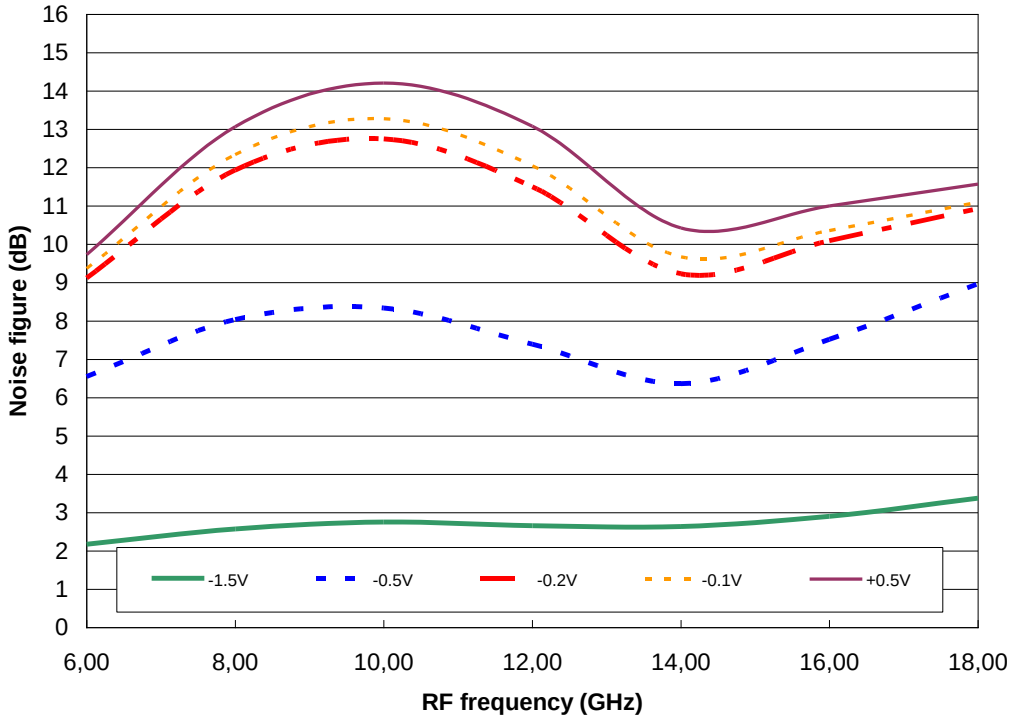
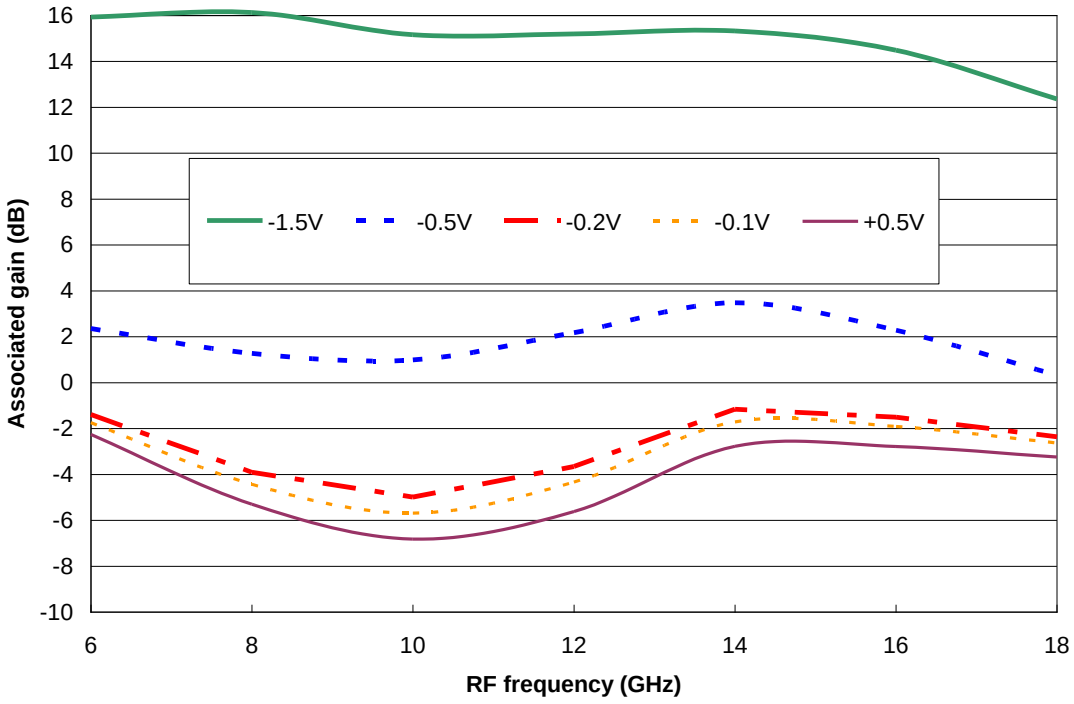
Noise figure @ Freq_IF= 2GHz versus V2,V3 at 25°C



Rem: The losses due to board are removed for noise measurements.

Associated gain @ Freq_IF= 2GHz versus V2,V3 at 25°C



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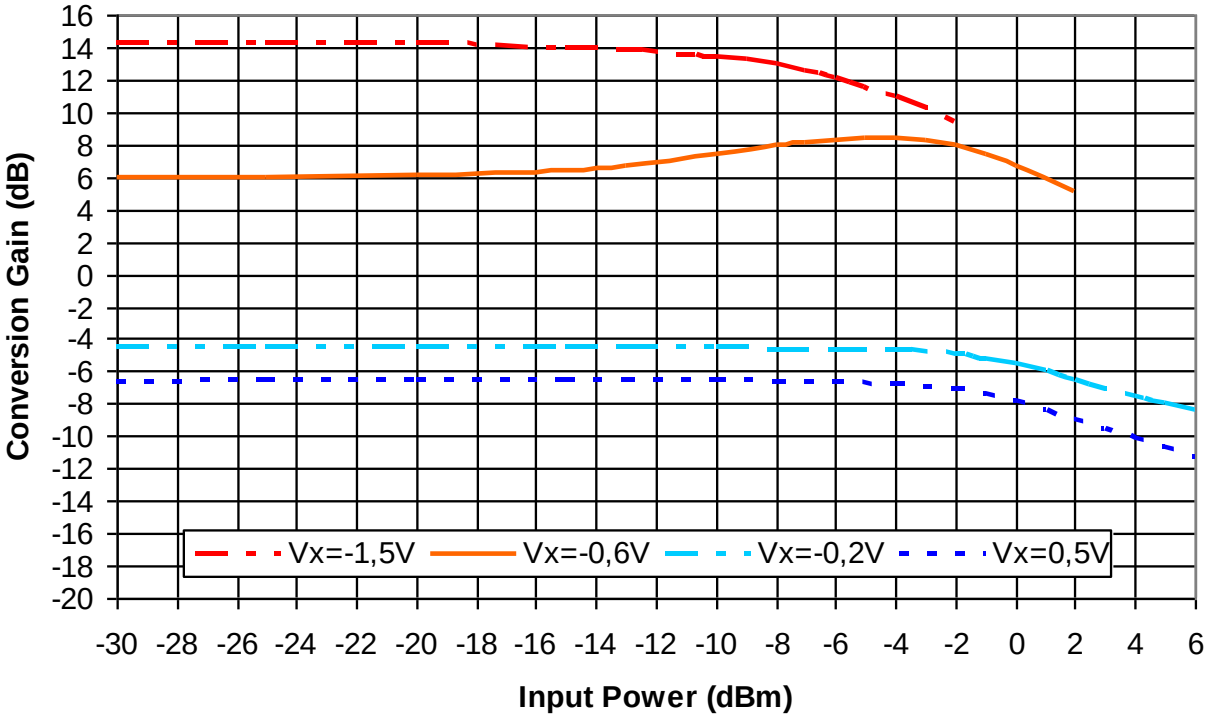
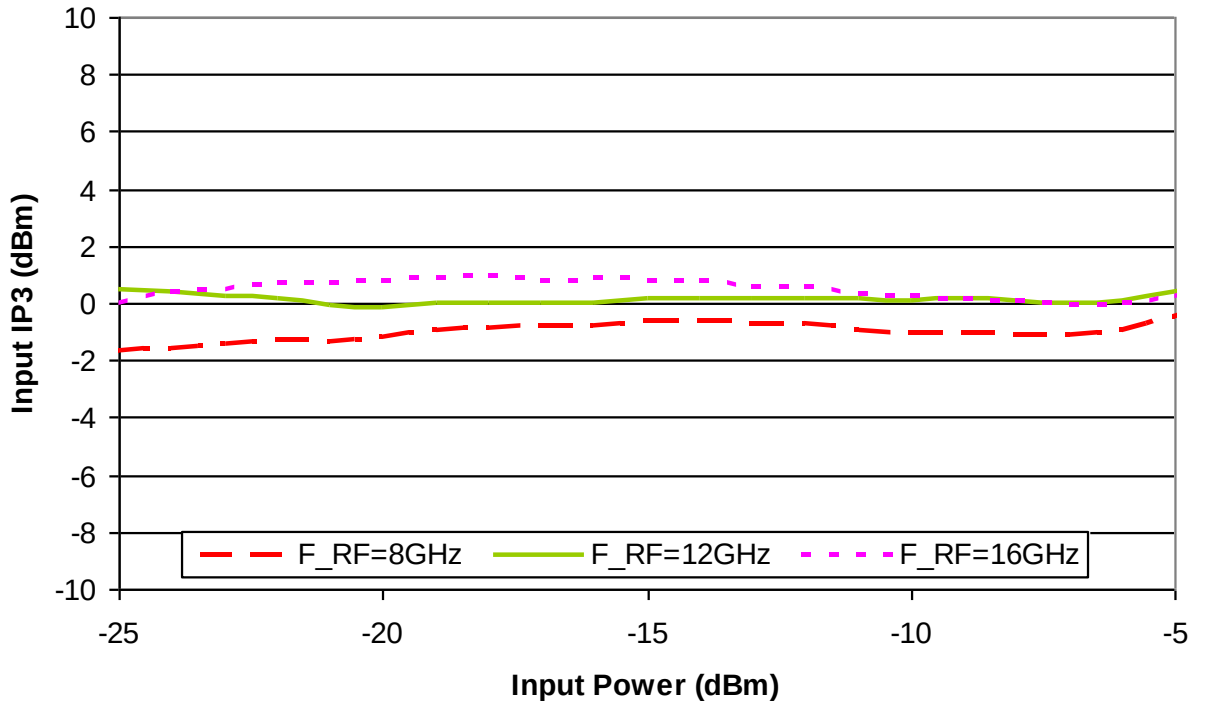
Compression (Sup. mode) @ Freq_RF= 12GHz, Freq_IF= 2GHz versus V2, V3 & P_RF



Input IP3 @Freq_IF= 3.5GHz, V2=V3=-1.5V & T=25°C versus FreqRF & P_RF (Double Carrier)



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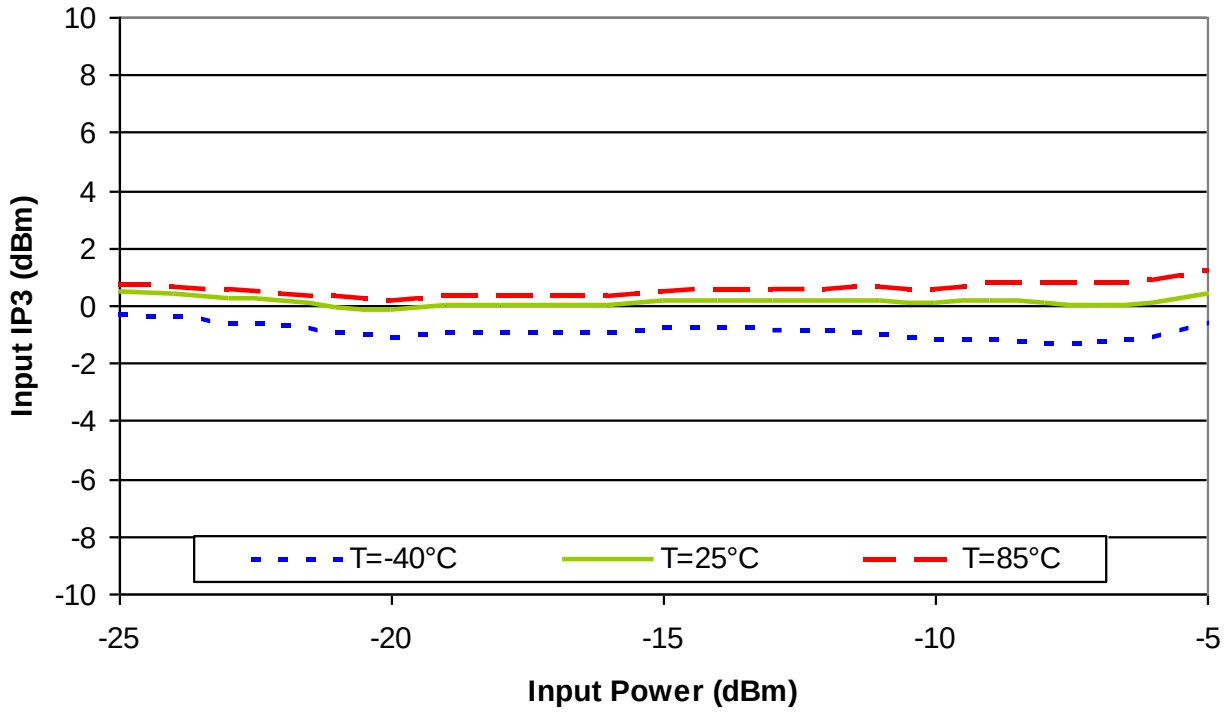
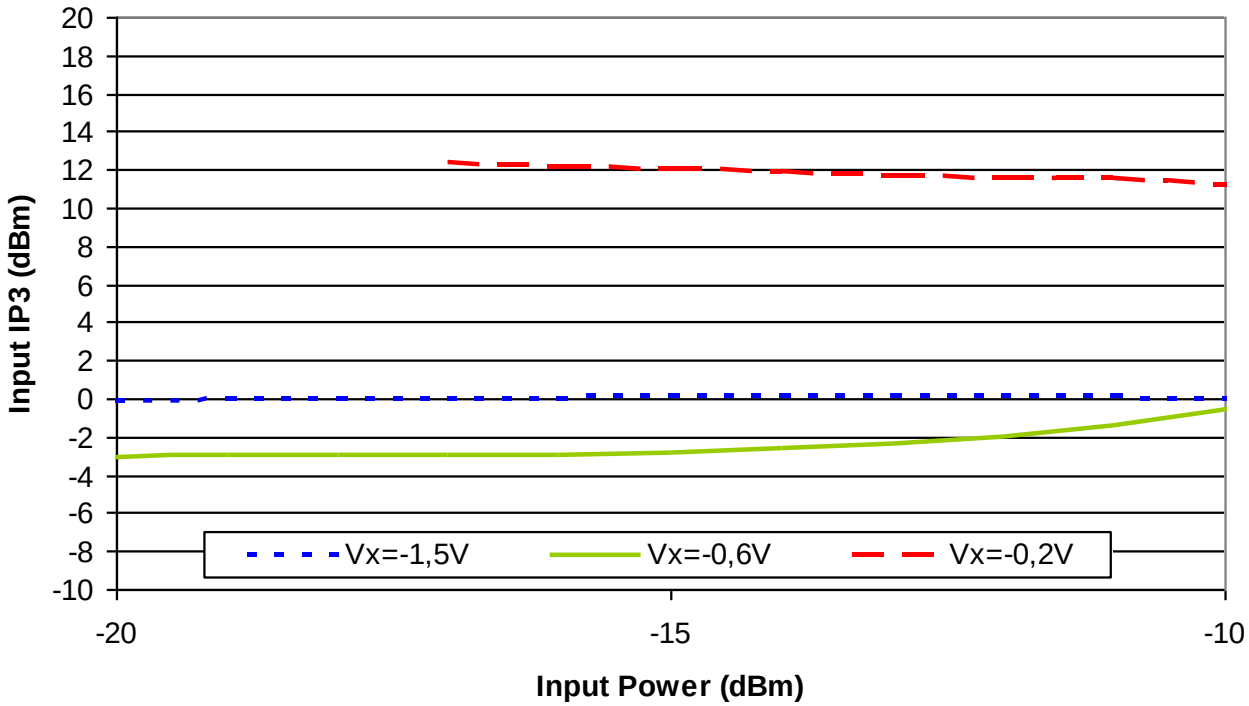
Input IP3 @Freq_RF=12GHz, Freq_IF= 3.5GHz & V2=V3=-1.5V versus T & P_RF (Double Carrier)



Input IP3 @Freq_RF=12GHz, Freq_IF= 3.5GHz & T=25°C versus V2,V3 & P_RF (Double Carrier)



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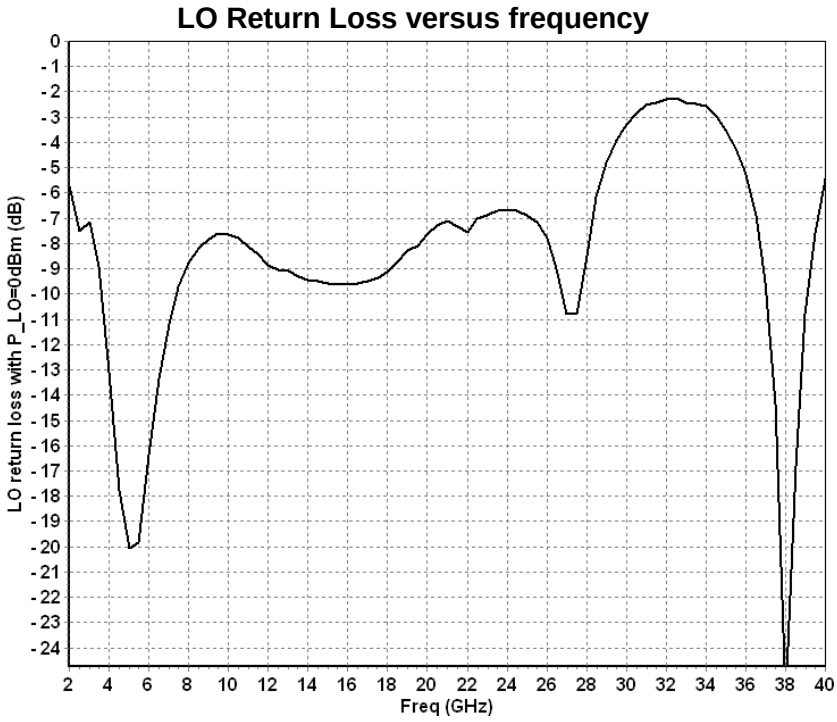

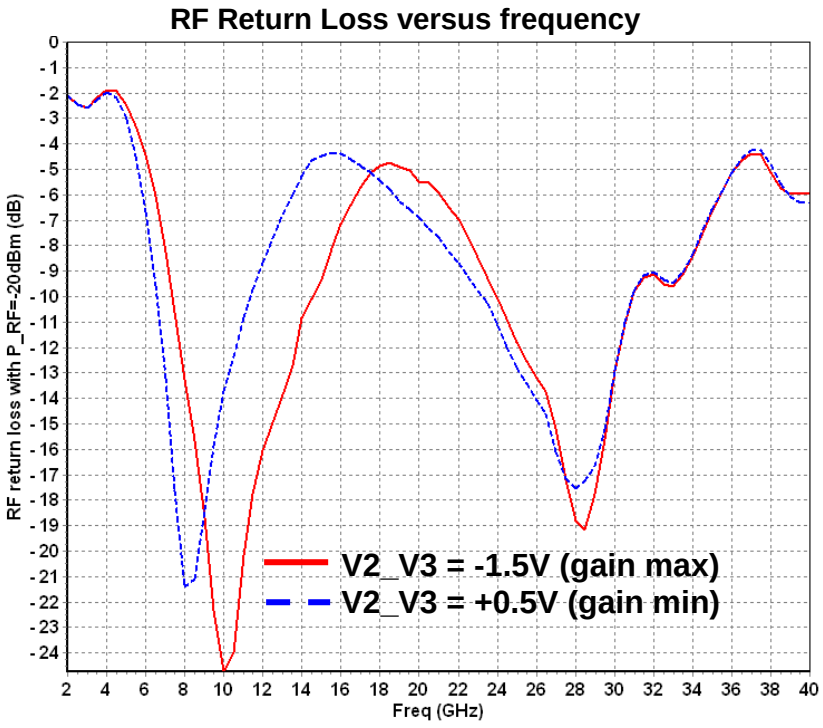

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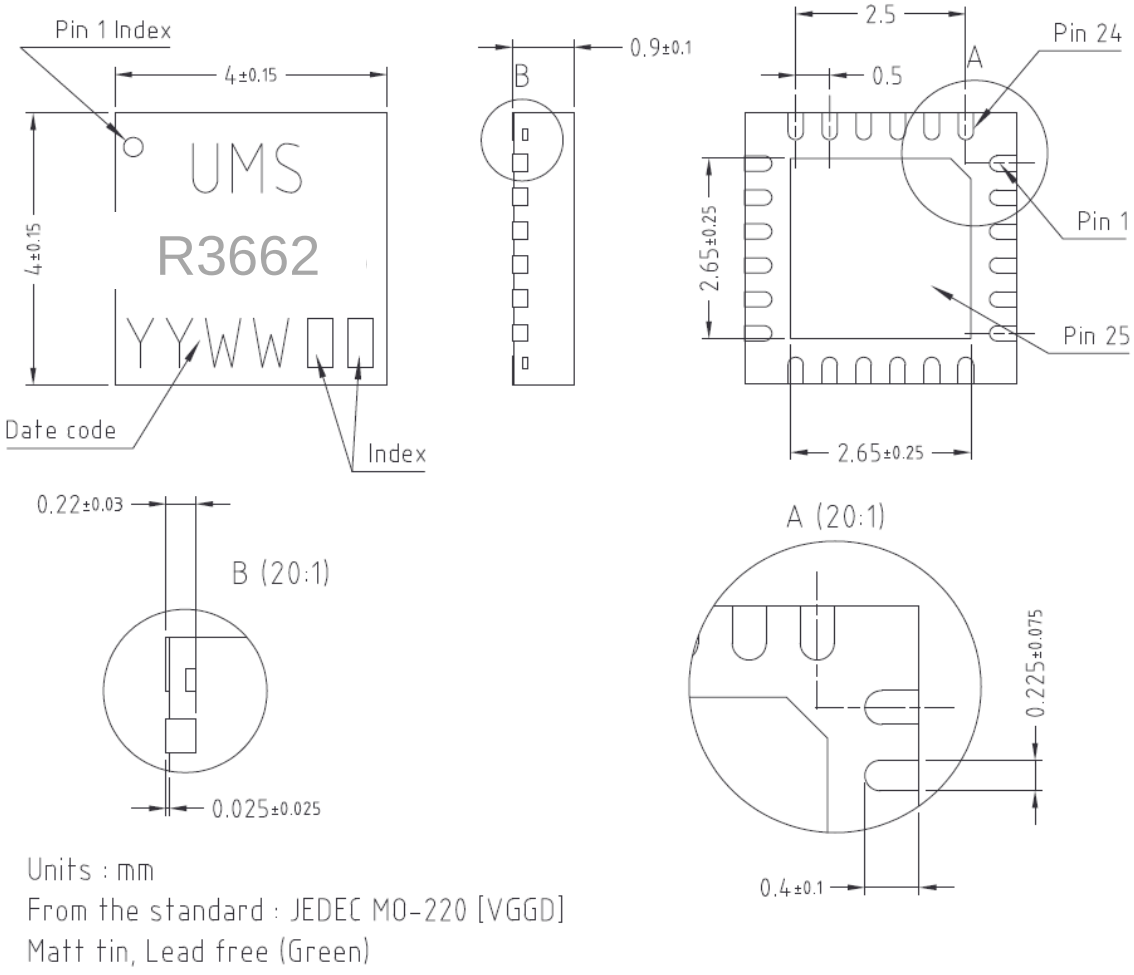
Package outline (1)



Matt tin, Lead Free	(Green)	1-	Nc	13-	Gnd
Units	mm	2-	Gnd	14-	Gnd
From the standard	JEDEC MO-220	3-	Gnd	15-	LO
	(VGGD)	4-	RF	16-	Gnd
25- GND		5-	Gnd	17-	Gnd
		6-	Gnd	18-	Nc
		7-	V2	19-	I
		8-	V3	20-	Gnd
		9-	VG	21-	Gnd
		10-	VGM	22-	Q
		11-	VD	23-	Nc
		12-	B	24-	Nc

(1)The package outline drawing included to this data-sheet is given for indication. Refer to the application note AN0017 available at https://www.ums-rf.com for exact package dimensions.

It is strongly recommended to ground all pins marked “Gnd” through the PCB board. Ensure that the PCB board is designed to provide the best possible ground to the package.

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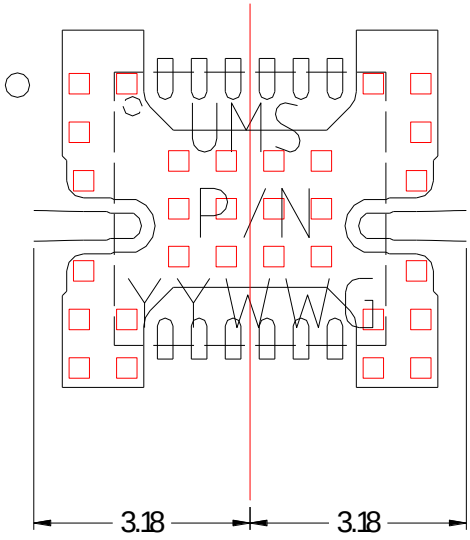
Definition of the Sij reference planes

The reference planes used for S measurements given above are symmetrica from the symmetrical axis of the package (se drawing beside). The input and outpu reference planes are located at 3.18mm offse (input wise and output wise respectively) fron this axis. Then, the given Sij parameter incorporate the land pattern of the evaluatio motherboard recommended at the page 16.



Recommended package footprint

Refer to the application note AN0017 available at https://www.ums-rf.com for package foot print recommendations.

SMD mounting procedure

The SMD leadless package has been designed for high volume surface mount PCB assembly process. The dimensions and footprint required for the PCB (motherboard) are given in the drawings above.

For the mounting process standard techniques involving solder paste and a suitable reflow process can be used. For further details, see application note AN0017.

Recommended environmental management

Refer to the application note AN0019 available at https://www.ums-rf.com for environmental data on UMS package products.

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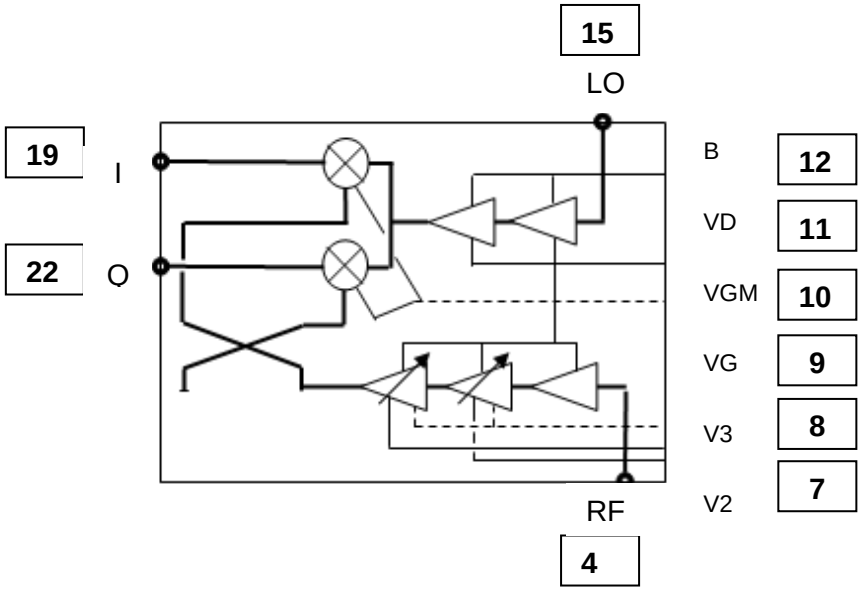
Notes

Due to ESD protection circuits on RF and LO inputs, an external capacitance might be requested to isolate the product from external voltage that could be present on these accesses. ESD protections are also implemented on gate accesses.
The DC connections do not include any decoupling capacitor in package, therefore it is mandatory to provide a good external DC decoupling on the PC board, as close as possible to the package.

Refer to the application note AN0020 available at https://www.ums-rf.com for general ESD recommendations.



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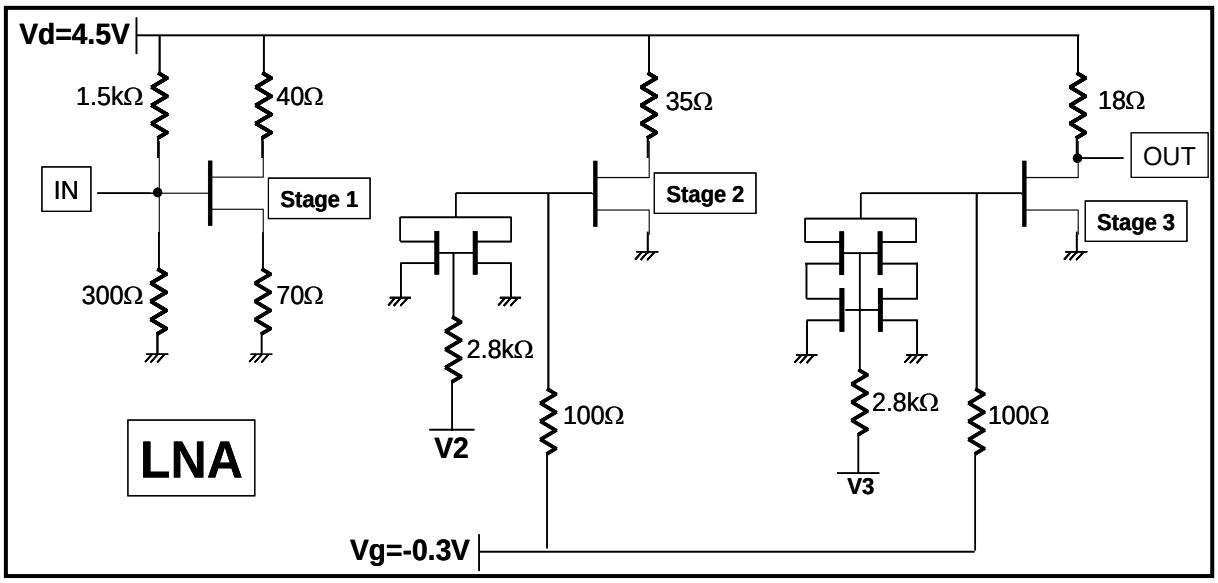
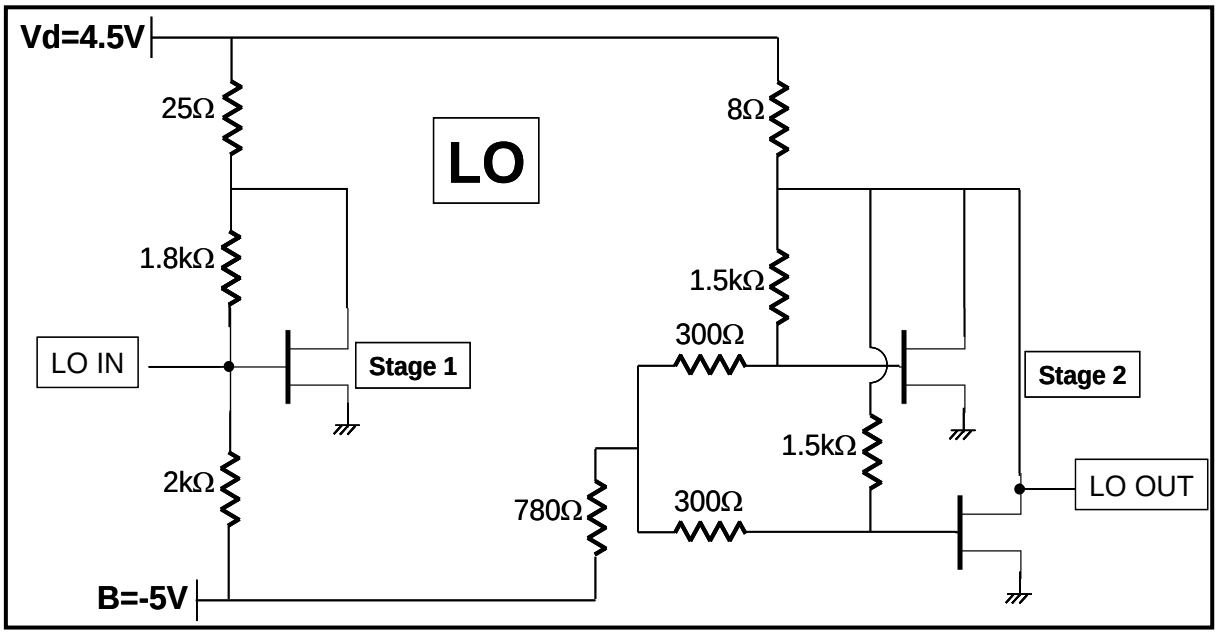
Notes

The biasing circuits of the stages of the circuit are given in the schemes below.





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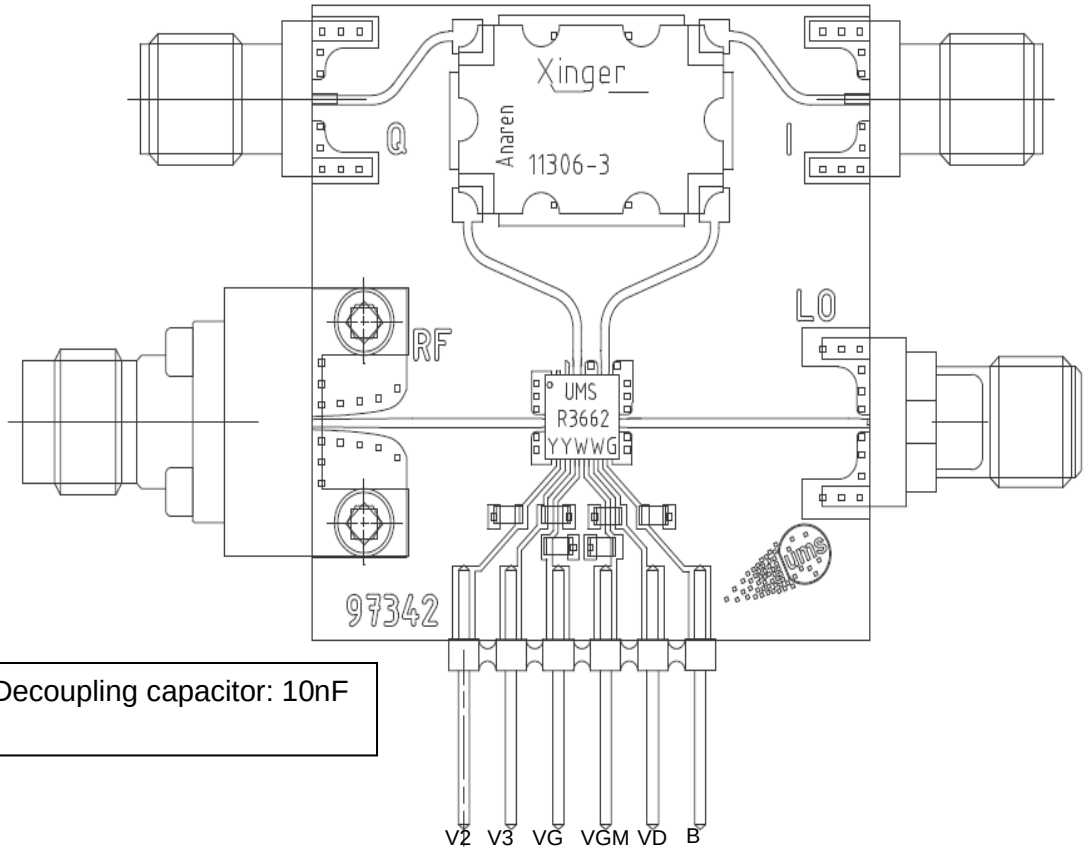
Evaluation mother board

- Compatible with the proposed footprint.
- Based on typically Ro4003 / 8mils or equivalent.
- Using a microstrip to coplanar transition to access the package.
- Recommended for the implementation of this product on a module board.
- Decoupling capacitors of 10nF ±10% are recommended for all DC accesses.
- (See application note AN0017 for details).

Proposed Assembly board "97342" for the 24L-QFN4x4 products characterization



Decoupling capacitor: 10nF

Ordering Information

QFN 4x4 RoHS compliant package: CHR3662-QDG/XY
Stick: XY = 20 Tape & reel: XY = 21

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